

## XtremeSense<sup>™</sup> TMR Coreless, Differential, and Contactless Current Sensor with Programmable Gain

### FEATURES AND BENEFITS

- User-programmable field range: □ 6 to 24 mT
- Preset magnetic field ranges:
  □ 0 to 6 mT
  □ ±6 mT
- $\Box \pm 0 \text{ m I}$
- Linear analog output voltage
- Common mode field rejection: -50 dB
- 1 MHz bandwidth
- Response time: <300 ns
- Reference voltage output for unipolar/bipolar field measurements
- Supply voltage: 3.0 to 3.6 V
- Low noise performance
- Filter pin to reduce noise on output
- Package options:
  B-lead SOIC
  - □ 8-lead TSSOP

### APPLICATIONS

- Solar/power inverters
- Battery management systems
- Industrial equipment
- PFC systems
- Power utility meters
- Power conditioner
- DC/DC converters/power supplies

### DESCRIPTION

The CT453 is a high-bandwidth and low-noise integrated zero-loss contactless current sensor that uses Allegro patented XtremeSense TMR technology to enable high-accuracy current measurements for many consumer, enterprise, and industrial applications. It supports two field ranges where the CT453 senses and translates the magnetic field into a linear analog output voltage.

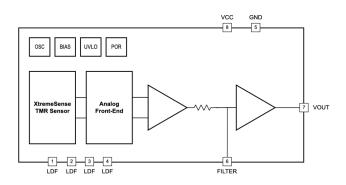
This coreless current sensor is not only small in size and simple to design, but it also provides effective common mode field rejection of more than -50 dB. This enables the CT453 to have greater than 90% immunity to stray magnetic fields, thus having almost no impact on the accuracy of the current measurement.

The device has less than 300 ns output response time while the current consumption is about 6.0 mA. The CT453 is equipped with a filter function to reduce the noise on the output pin.

The CT453 is assembled in an 8-lead SOIC package and a low-profile, industry-standard 8-lead TSSOP package that are both green and RoHS compliant.

### PACKAGES:





### Figure 1: CT453 Functional Block Diagram for SOIC-8

### FUNCTIONAL BLOCK DIAGRAMS

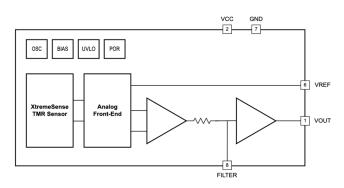


Figure 2: CT453 Functional Block Diagram for TSSOP-8

### **Table of Contents**

Features and Benefits	. 1
Description	. 1
Applications	. 1
Packages	. 1
Functional Block Diagrams	. 1
Selection Guide	. 2
Evaluation Board Selection Guide	. 2
Absolute Maximum Ratings	. 3
Recommended Operating Conditions	. 3
Application Diagrams	. 4
Pinout Diagrams and Terminal Lists	. 5

Electrical Characteristics	7
Functional Description	13
XtremeSense TMR Current Sensor Location	17
Package Outline Drawings	18
Tape and Reel Pocket Drawings and Dimensions	20
Package Information	
Device Markings	23
Part Ordering Number Legend	23
Revision History	25

#### SELECTION GUIDE

Part Number	Automotive Grade	Range (mT)	Operating Temperature Range (°C)	Package	Packing
BIPOLAR SENSITIVI	ГҮ		•	· · · · ·	
CT453-H06MRSN08	_	±6	-40 to 125	8-lead SOIC 4.89 mm × 6.00 mm × 1.62 mm	Tape and Reel
CT453-H06MRTS08	-	±6	-40 to 125	8-lead TSSOP 3.00 mm × 6.40 mm × 1.10 mm	Tape and Reel
UNIPOLAR SENSITIV	ΊΤΥ				
CT453-H06DRSN08	-	6	-40 to 125	8-lead SOIC 4.89 mm × 6.00 mm × 1.62 mm	Tape and Reel
CT453-H06DRTS08	-	6	-40 to 125	8-lead TSSOP 3.00 mm × 6.40 mm × 1.10 mm	Tape and Reel
PROGRAMMABLE SI	ENSITIVITY				
CT453-H00MRSN08	_	±6 to ±24	40 to 125	8-lead SOIC	Tape and
CT453-H00DRSN08	_	6 to 24	-40 10 125	-40 to 125 4.89 mm × 6.00 mm × 1.62 mm	
CT453-H00MRTS08	_	±6 to ±24	40 to 105	8-lead TSSOP	Tape and
CT453-H00DRTS08	_	6 to 24	40 to 125	3.00 mm × 6.40 mm × 1.10 mm	Reel

#### **EVALUATION BOARD SELECTION GUIDE**

Part Number	Magnetic Field Range (mT)	Current Carrying Conductor	Operating Temperature Range (°C)	Package
CTD453-BB-06U	0 to 6	Busbar	-40 to 125	
CTD453-BB-06B	±6	Dusbai		8-lead SOIC
CTD453-PT-06U	0 to 6	PCB Trace		4.89 mm × 6.00 mm × 1.62 mm
CTD453-PT-06B	±6	PCD Trace		



### ABSOLUTE MAXIMUM RATINGS <sup>[1]</sup>

Characteristic	Symbol	Notes	Rating	Unit
Supply Voltage Strength	V <sub>CC</sub>		-0.3 to 6.0	V
Analog Input/Output Pins Maximum Voltage	V <sub>I/O</sub>		-0.3 to V <sub>CC</sub> + 0.3 <sup>[2]</sup>	V
Electrostatic Discharge Dratestian Level	ESD	Human Body Model (HBM) per JESD22-A114	±2.0 (min)	kV
Electrostatic Discharge Protection Level	ESD	Charged Device Model (CDM) per JESD22-C101	±0.5 (min)	kV
Junction Temperature	TJ		-40 to 150	°C
Storage Temperature	T <sub>STG</sub>		–65 to 155	°C
Lead Soldering Temperature	TL	10 seconds	260	°C

<sup>[1]</sup> Stresses exceeding the absolute maximum ratings may damage the CT453 and may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

 $^{[2]}$  The lower of V\_CC + 0.3 V or 6.0 V.

#### **RECOMMENDED OPERATING CONDITIONS**<sup>[1]</sup>

Characteristic	Symbol	Notes	Min.	Тур.	Max.	Unit
Supply Voltage Range	V <sub>CC</sub>		3.0	3.3	3.6	V
Output Voltage Range	V <sub>OUT</sub>		0	-	V <sub>CC</sub>	V
Output Current	I <sub>OUT</sub>		_	-	±1.0	mA
Operating Ambient Temperature	T <sub>A</sub>		-40	25	125	°C

[1] The Recommended Operating Conditions table defines the conditions for actual operation of the CT453. Recommended operating conditions are specified to ensure optimal performance to the specifications. Allegro does not recommend exceeding them or designing to absolute maximum ratings.



### **APPLICATION DIAGRAMS**

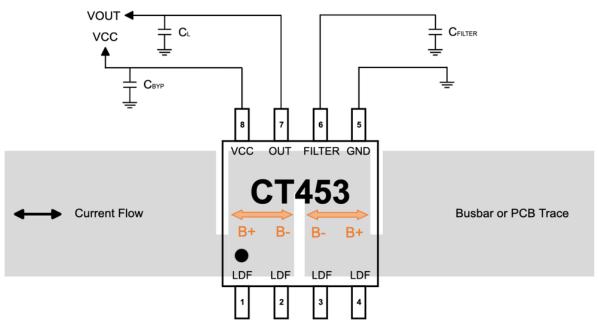
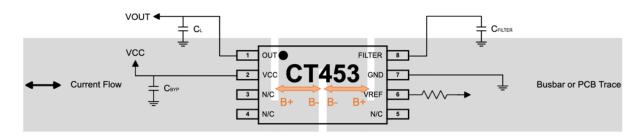


Figure 3: CT453 Application Diagram for SOIC-8

#### Table 1: Recommended External Components

Component	Description	Vendor and Part Number	Min.	Тур.	Max.	Unit
C <sub>BYP</sub>	1.0 µF, X5R or better	Murata GRM155C81A105KA12	-	1.0	-	μF
C <sub>FILTER</sub>	Various, X5R or better	Murata	_	Figure 14	-	pF

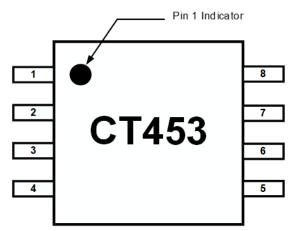


#### **Table 2: Recommended External Components**

Component	Description	Vendor and Part Number	Min.	Тур.	Max.	Unit
C <sub>BYP</sub>	1.0 µF, X5R or better	Murata GRM155C81A105KA12	-	1.0	-	μF
C <sub>FILTER</sub>	Various, X5R or better	Murata	_	Figure 14	_	pF
R <sub>VREF</sub>	10 kΩ resistor	Various	-	10	_	kΩ



### PINOUT DIAGRAMS AND TERMINAL LISTS

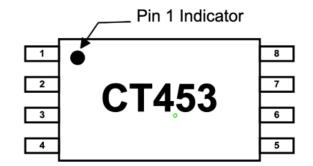


#### Figure 5: CT453 Pinout Diagram for 8-lead SOIC Package (Top-Down View)

#### **Terminal List**

Number	Name	Function
1, 2, 3, 4	LDF	Lead frame Pin – A single (1) LDF pin should be connected to GND. The other three (3) LDF pins should be left unconnected to avoid ground loops through the lead frame.
5	GND	Ground.
6	FILTER	Filter pin to improve noise performance by connecting an external capacitor to set the cutoff frequency. No connect if the FILTER pin is not used.
7	OUT	Analog output voltage that represents the measured current/field.
8	VCC	Supply voltage.





### Figure 6: CT453 Pinout Diagram for 8-lead TSSOP Package (Top-Down View)

#### **Terminal List**

Number	Name	Function
1	OUT	Analog output voltage that represents the measured current/field.
2	VCC	Supply voltage.
3, 4, 5	NC	No connect (do not use).
6	VREF	Reference voltage output. If not used, then do not connect.
7	GND	Ground.
8	FILTER	Filter pin to improve noise performance by connecting an external capacitor to set the cutoff frequency. No connect if the FILTER pin is not used.



## **ELECTRICAL CHARACTERISTICS:** Valid for $V_{CC}$ = 3.0 to 3.6 V, $C_{BYP}$ = 1.0 µF, and $T_A$ = -40°C to 125°C, typical values are $V_{CC}$ = 3.3 V and $T_A$ = 25°C, unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
POWER SUPPLIES						
Supply Current	I <sub>CC</sub>	f <sub>BW</sub> = 1 MHz, no load, B <sub>OP</sub> = 0 mT	_	6.0	9.0	mA
OUT Maximum Drive Capability	I <sub>OUT</sub>	OUT covers 10% to 90% of V <sub>CC</sub> span	-1.0	-	+1.0	mA
OUT Capacitive Load	C <sub>L_OUT</sub>		-	-	100	pF
OUT Resistive Load	R <sub>L_OUT</sub>		-	100	_	kΩ
Internal Filter Resistance <sup>[1]</sup>	R <sub>FILTER</sub>		-	15	_	kΩ
Power Supply Rejection Ratio <sup>[1]</sup>	PSRR		_	35	_	dB
Sensitivity Power Supply Rejection Ratio <sup>[1]</sup>	SPSRR		_	35	_	dB
Offset Power Supply Rejection Ratio <sup>[1]</sup>	OPSRR		-	40	_	dB
Common Mode Field Rejection Ratio [1]	CMFRR		-	-50	_	dB
ANALOG OUTPUT (OUT)			·			
OUT Voltage Linear Range	V <sub>OUT</sub>	$V_{SIG_{AC}} = \pm 2.00 \text{ V}, V_{SIG_{DC}} = +4.00 \text{ V}$	0.65	-	2.65	V
Output High Saturation Voltage	V <sub>OUT_SAT</sub>	T <sub>A</sub> = 25°C	V <sub>CC</sub> - 0.30	V <sub>CC</sub> - 0.25	_	V
REFERENCE VOLTAGE (VREF) FOR	R TSSOP-8	ONLY	<u>~</u>			·
Deference Veltage	V	Unipolar variant	-	0.65	_	V
Reference Voltage	V <sub>REF</sub>	Bipolar variant	-	1.65	_	V
VREF Maximum Drive Capability	I <sub>VREF</sub>		-50	-	50	μA
VREF Capacitive Load	$C_{L_{VREF}}$		_	_	10	pF
VREF Resistive Load	$R_{L_{VREF}}$		_	10	_	kΩ
TIMINGS						
Power-On Time	t <sub>ON</sub>	$V_{CC} \ge 4.0 V$	_	100	200	μs
Rise Time <sup>[1]</sup>	t <sub>RISE</sub>	$B_{OP} = B_{OP(MAX)}, T_A = 25^{\circ}C, C_L = 100 \text{ pF}$	_	200	_	ns
Response Time <sup>[1]</sup>	t <sub>RESPONSE</sub>	$B_{OP} = B_{OP(MAX)}, T_A = 25^{\circ}C, C_L = 100 \text{ pF}$	-	300	_	ns
Propagation Delay <sup>[1]</sup>	t <sub>DELAY</sub>	$B_{OP} = B_{OP(MAX)}, T_A = 25^{\circ}C, C_L = 100 \text{ pF}$	_	250	_	ns
PROTECTION						
	M	Rising V <sub>CC</sub>	_	2.50	_	V
Undervoltage Lockout	V <sub>UVLO</sub>	Falling V <sub>CC</sub>	_	2.45	_	V
UVLO Hysteresis	V <sub>UV_HYS</sub>		_	50	_	mV

<sup>[1]</sup> Guaranteed by design and characterization; not tested in production.



### ELECTRICAL CHARACTERISTICS

 $V_{CC}$  = 3.3 V,  $T_{A}$  = 25°C, and  $C_{BYP}$  = 1.0  $\mu F$  (unless otherwise specified)

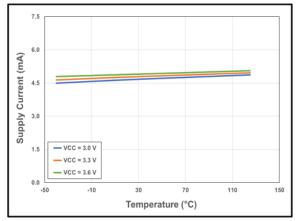


Figure 7: CT453 Supply Current vs. Temperature vs. Supply Voltage

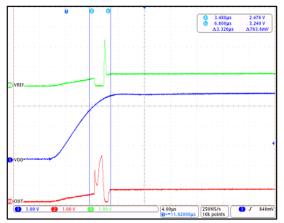


Figure 9: CT453 Startup Waveforms for V<sub>OQ</sub> = 0.65 V (Unipolar Field)

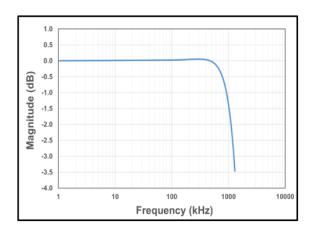


Figure 8: CT453 Bandwidth with C<sub>FILTER</sub> = 1.0 pF

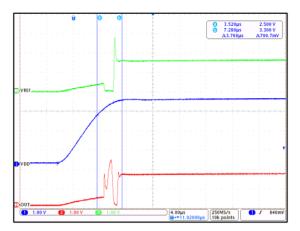


Figure 10: CT453 Startup Waveforms for V<sub>OQ</sub> = 1.65 V (Bipolar Field)



## **CT453-x06DR: 0 to 6 mT – ELECTRICAL CHARACTERISTICS** <sup>[1]</sup>: Valid for $V_{CC}$ = 3.0 to 3.6 V, $C_{BYP}$ = 1.0 µF, and $T_A$ = -40°C to 125°C, typical values are $V_{CC}$ = 3.3 V and $T_A$ = 25°C, unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Magnetic Field Range	B <sub>RNG</sub>		0	-	6	mT
Voltage Output Quiescent	V <sub>OQ</sub>	T <sub>A</sub> = 25°C, B <sub>OP</sub> = 0 mT	-	0.650	_	V
Sensitivity	S	$B_{RNG(MIN)} < B_{OP} < B_{RNG(MAX)}$	-	333.3	_	mV/mT
Bandwidth [2]	f <sub>BW</sub>	Small Signal = –3 dB	-	1.0	_	MHz
Naisa [2]		$T = 25^{\circ}C$ f = 100 kHz	-	0.81	_	mV <sub>RMS</sub>
Noise <sup>[2]</sup>	e <sub>N</sub>	T <sub>A</sub> = 25°C, f <sub>BW</sub> = 100 kHz	-	2.42	_	μT <sub>RMS</sub>
OUT ACCURACY PERFORMANCE						
Linearity Error	E <sub>LIN</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to 125°C	-	±0.3	_	% FS
Sanaitivity Tomporatura Drift	E	$B_{OP} = B_{OP(MAX)}$ , $T_A = 25^{\circ}C$ to $125^{\circ}C$	-	±1.4	_	%
Sensitivity Temperature Drift	E <sub>SENS</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = 25^{\circ}C$ to $-40^{\circ}C$	-	±2.2	_	%
Offset Voltage Error	V <sub>OE</sub>	B <sub>OP</sub> = 0 mT, T <sub>A</sub> = 25°C	-	±4	—	mV
Offect Voltage Temperature Drift	M	B <sub>OP</sub> = 0 mT, T <sub>A</sub> = 25°C to 125°C	-	±13	_	mV
Offset Voltage Temperature Drift	V <sub>OE_Tdrift</sub>	$B_{OP} = 0 \text{ mT}, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	-	±15	_	mV
LIFETIME DRIFT						
Sensitivity Error Including Lifetime Drift	E <sub>SENS(DRIFT)</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to $125^{\circ}C$	-	±3	_	%
Offset Voltage Error Including Lifetime Drift	V <sub>OE(DRIFT)</sub>	$B_{OP} = 0 \text{ mT}, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	-	±20	_	mV

<sup>[1]</sup> Typical values are the mean ±3 sigma of a test sample population. These are formatted as mean ±3 sigma.

<sup>[2]</sup> Guaranteed by design and characterization; not tested in production.

### ELECTRICAL CHARACTERISTICS FOR CT453-x06DR

 $V_{CC}$  = 3.3 V, T<sub>A</sub> = 25°C, and C<sub>BYP</sub> = 1.0 µF (unless otherwise specified)

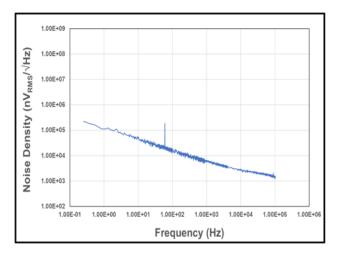


Figure 11: Noise Density vs. Frequency



CT453-x06MR: ±6 mT – ELECTRICAL CHARACTERISTICS <sup>[1]</sup>: Valid for  $V_{CC}$  = 3.0 to 3.6 V,  $C_{BYP}$  = 1.0 µF, and  $T_A$  = -40°C to 125°C, typical values are  $V_{CC}$  = 3.3 V and  $T_A$  = 25°C, unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Magnetic Field Range	B <sub>RNG</sub>		-6	-	6	mT
Voltage Output Quiescent	V <sub>OQ</sub>	T <sub>A</sub> = 25°C, B <sub>OP</sub> = 0 mT	-	1.650	_	V
Sensitivity	S	$B_{RNG(MIN)} < B_{OP} < B_{RNG(MAX)}$	-	166.7	_	mV/mT
Bandwidth <sup>[2]</sup>	f <sub>BW</sub>	Small Signal = –3 dB	-	1.0	_	MHz
Ni-i [2]	_		-	0.45	_	mV <sub>RMS</sub>
Noise <sup>[2]</sup>	e <sub>N</sub> T <sub>A</sub> =	T <sub>A</sub> = 25°C, f <sub>BW</sub> = 100 kHz	_	2.69	_	μT <sub>RMS</sub>
OUT ACCURACY PERFORMANCE	·	·				
Linearity Error	E <sub>LIN</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to $125^{\circ}C$	_	±0.3	_	% FS
	-	$B_{OP} = B_{OP(MAX)}$ , $T_A = 25^{\circ}C$ to $125^{\circ}C$	-	±1.4	_	%
Sensitivity Temperature Drift	E <sub>SENS</sub>	$B_{OP} = B_{OP(MAX)}, T_A = 25^{\circ}C \text{ to } -40^{\circ}C$	-	±2.2	_	%
Offset Voltage Error	V <sub>OE</sub>	B <sub>OP</sub> = 0 mT, T <sub>A</sub> = 25°C	-	±4	_	mV
		B <sub>OP</sub> = 0 mT, T <sub>A</sub> = 25°C to 125°C	-	±13	_	mV
Offset Voltage Temperature Drift	V <sub>OE_Tdrift</sub>	$B_{OP} = 0 \text{ mT}, T_A = 25^{\circ}\text{C to} -40^{\circ}\text{C}$	-	±15	_	mV
LIFETIME DRIFT						
Sensitivity Error Including Lifetime Drift	E <sub>SENS(DRIFT)</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to $125^{\circ}C$	-	±3	_	%
Offset Voltage Error Including Lifetime Drift	V <sub>OE(DRIFT)</sub>	$B_{OP} = 0 \text{ mT}, T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$	-	±20	_	mV

<sup>[1]</sup> Typical values are the mean ±3 sigma of a test sample population. These are formatted as mean ±3 sigma. <sup>[2]</sup> Guaranteed by design and characterization; not tested in production.

### **ELECTRICAL CHARACTERISTICS FOR CT453-x06MR**

 $V_{CC}$  = 3.3 V,  $T_A$  = 25°C, and  $C_{BYP}$  = 1.0 µF (unless otherwise specified)

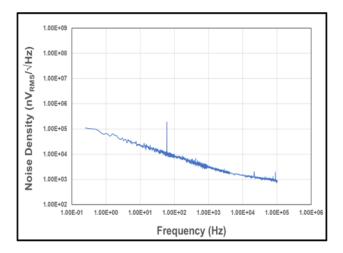


Figure 12: Noise Density vs. Frequency



## CT453-x00MR: Programmable Gain – ELECTRICAL CHARACTERISTICS <sup>[1]</sup>: Valid for V<sub>CC</sub> = 3.0 to 3.6 V, C<sub>BYP</sub> = 1.0 $\mu$ F, and T<sub>A</sub> = -40°C to 125°C, typical values are V<sub>CC</sub> = 3.3 V and T<sub>A</sub> = 25°C, unless otherwise specified

Characteristics Symbol		Test Conditions	Min.	Тур.	Max.	Unit
Programmable Magnetic Field Panga	В		±6	-	±8	mT
Programmable Magnetic Field Range	B <sub>PRNG</sub>		±12	-	±24	mT
Voltage Output Quiescent	V <sub>OQ</sub>	T <sub>A</sub> = 25°C, B <sub>OP</sub> = 0 mT	_	1.650	-	V
Maximum Programmable Sensitivity	S <sub>PMAX</sub>	$B_{RNG(MIN)} < B_{OP} < B_{RNG(MAX)}$	_	333.3	-	mV/mT
Minimum Programmable Sensitivity	S <sub>PMIN</sub>	$B_{RNG(MIN)} < B_{OP} < B_{RNG(MAX)}$	_	83.4	-	mV/mT
Bandwidth <sup>[2]</sup>	f <sub>BW</sub>	Small Signal = –3 dB	_	1.0	_	MHz
OUT ACCURACY PERFORMANCE						
Linearity Error	E <sub>LIN</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to $125^{\circ}C$	_	±0.3	_	% FS
Sensitivity Temperature Drift	E	$B_{OP} = B_{OP(MAX)}$ , $T_A = 25^{\circ}C$ to $125^{\circ}C$	-	±1.4	-	%
	E <sub>SENS</sub>	$B_{OP} = B_{OP(MAX)}, T_A = 25^{\circ}C \text{ to } -40^{\circ}C$	-	±2.2	-	%
Offset Voltage Error	V <sub>OE</sub>	B <sub>OP</sub> = 0 mT, T <sub>A</sub> = 25°C	-	±4	-	mV
Offact Voltage Temperature Drift	V	$B_{OP} = 0 \text{ mT}, T_A = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±13	-	mV
Offset Voltage Temperature Drift	V <sub>OE_Tdrift</sub>	$B_{OP} = 0 \text{ mT}, T_A = 25^{\circ}\text{C} \text{ to } -40^{\circ}\text{C}$	_	±15	-	mV
LIFETIME DRIFT						
Sensitivity Error Including Lifetime Drift	E <sub>SENS(DRIFT)</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to $125^{\circ}C$	_	±3	_	%
Offset Voltage Error Including Lifetime Drift	V <sub>OE(DRIFT)</sub>	$B_{OP} = 0 \text{ mT}, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±20	_	mV

 $^{[1]}$  Typical values are the mean  $\pm 3$  sigma of a test sample population. These are formatted as mean  $\pm 3$  sigma.

<sup>[2]</sup> Guaranteed by design and characterization; not tested in production.

### **Calibration Description**

The CT453-x00MR is factory-trimmed for sensitivity and offset temperature drift. The sensor provides the ability to adjust gain to allow for all the mechanical tolerances during manufacturing. Gain calibration is recommended to be performed at room temperature (25°C) using the Allegro CTC4000 Calibration Box.



## CT453-x00DR: Programmable Gain – ELECTRICAL CHARACTERISTICS <sup>[1]</sup>: Valid for V<sub>CC</sub> = 3.0 to 3.6 V, C<sub>BYP</sub> = 1.0 $\mu$ F, and T<sub>A</sub> = -40°C to 125°C, typical values are V<sub>CC</sub> = 3.3 V and T<sub>A</sub> = 25°C, unless otherwise specified

Characteristics Symbol		Test Conditions	Min.	Тур.	Max.	Unit
Programmable Magnetic Field Pange	P		6	-	8	mT
Programmable Magnetic Field Range	B <sub>PRNG</sub>		12	-	24	mT
Voltage Output Quiescent	V <sub>OQ</sub>	T <sub>A</sub> = 25°C, B <sub>OP</sub> = 0 mT	_	0.650	_	V
Maximum Programmable Sensitivity	S <sub>PMAX</sub>	$B_{RNG(MIN)} < B_{OP} < B_{RNG(MAX)}$	_	666.7	_	mV/mT
Minimum Programmable Sensitivity	S <sub>PMIN</sub>	$B_{RNG(MIN)} < B_{OP} < B_{RNG(MAX)}$	_	166.7	_	mV/mT
Bandwidth <sup>[2]</sup>	f <sub>BW</sub>	Small Signal = –3 dB	_	1.0	_	MHz
OUT ACCURACY PERFORMANCE						
Linearity Error	E <sub>LIN</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to $125^{\circ}C$	_	±0.3	_	% FS
Sancitivity Tomporature Drift	F	$B_{OP} = B_{OP(MAX)}$ , $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1.4	_	%
Sensitivity Temperature Drift	E <sub>SENS</sub>	$B_{OP} = B_{OP(MAX)}, T_A = 25^{\circ}C \text{ to } -40^{\circ}C$	-	±2.2	_	%
Offset Voltage Error	V <sub>OE</sub>	B <sub>OP</sub> = 0 mT, T <sub>A</sub> = 25°C	_	±4	_	mV
		$B_{OP} = 0 \text{ mT}, T_A = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±13	_	mV
Offset Voltage Temperature Drift	V <sub>OE_Tdrift</sub>	$B_{OP} = 0 \text{ mT}, T_A = 25^{\circ}\text{C to} -40^{\circ}\text{C}$	_	±15	_	mV
LIFETIME DRIFT						
Sensitivity Error Including Lifetime Drift	E <sub>SENS(DRIFT)</sub>	$B_{OP} = B_{OP(MAX)}$ , $T_A = -40^{\circ}C$ to $125^{\circ}C$	_	±3	_	%
Offset Voltage Error Including Lifetime Drift	V <sub>OE(DRIFT)</sub>	$B_{OP} = 0 \text{ mT}, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±20	_	mV

 $^{[1]}$  Typical values are the mean  $\pm 3$  sigma of a test sample population. These are formatted as mean  $\pm 3$  sigma.

<sup>[2]</sup> Guaranteed by design and characterization; not tested in production.

### **Calibration Description**

The CT453-x00DR is factory-trimmed for sensitivity and offset temperature drift. The sensor provides the ability to adjust gain to allow for all the mechanical tolerances during manufacturing. Gain calibration is recommended to be performed at room temperature (25°C) using the Allegro CTC4000 Calibration Box.



### FUNCTIONAL DESCRIPTION

### Overview

The CT453 is a very high accuracy coreless and contactless current sensor that can sense magnetic fields from 6 to 24 mT. The device has high sensitivity and a wide dynamic range with excellent accuracy across temperature. This current sensor supports two field ranges as standard and can also be user-programmable up to 24 mT:

• 0 to 6 mT • ±6 mT

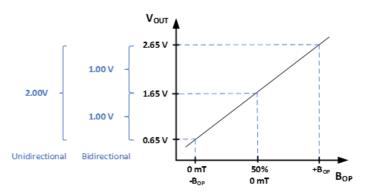
The CT453 is also available in a user-programmable variant which enables end-of-line calibration of gain. While the sensor is pre-programmed to adjust sensitivity and offset temperature drift, the ability to adjust gain relaxes mechanical tolerances during sensor mounting.

When current is flowing through a busbar above or below the CT453, the XtremeSense TMR sensor inside the chip senses the field which in turn generates a differential voltage signals that then goes through the Analog Front-End (AFE) to output a current measurement.

The chip is designed to enable a fast response time of 300 ns for the current measurement from the OUT pin as the bandwidth for the CT453 is 1.0 MHz. Even with a high bandwidth, the chip consumes a minimal amount of power.

### Linear Output Current Measurement

The CT453 provides a continuous linear analog output voltage which represents the current measurement. The output voltage range of OUT is from 0.65 to 2.65 V with a  $V_{OQ}$  of 0.65 V and 1.65 V for unidirectional and bidirectional currents, respectively. Figure 13 illustrates the output voltage range of the OUT pin as a function of the measured current.





### Voltage Reference Function (VREF)

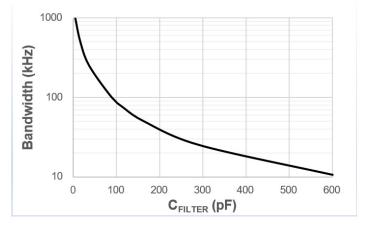
The CT453 in TSSOP-8 package has a reference voltage (VREF) pin that may be used as an output voltage reference for AC or DC field/current measurements. The VREF pin should be connected to a buffer circuit.

If VREF is not used, then it should be left unconnected.

### Filter Function (FILTER)

The CT453 has a pin for the FILTER function which will enable it to improve the noise performance by changing the cutoff frequency. The bandwidth of the CT453 is 1.0 MHz; however, adding a capacitor to the FILTER pin—which will be in-series with an internal resistance of approximately 15 k $\Omega$ —will set the cutoff frequency to reduce noise. Figure 14 shows the capacitor values required to achieve different cutoff frequencies.

Experimentally measured bandwidth does not necessarily match the calculated bandwidth value obtained by using the equation  $f_{BW} = \frac{1}{2\pi RC}$  because of the parasitic capacitances due to PCB manufacturing and layout. This is further impacted by the small, picofarad level C<sub>FILTER</sub> recommendations.



### Figure 14: Bandwidth vs. C<sub>FILTER</sub> Common Mode Field Rejection (CMFR) Mode

The CT453 has a built-in CMFR mode that combines the design ease of contactless current sensing with excellent common mode field rejection. This is achieved by placing notches in the currentcarrying busbar or PCB trace to generate a differential magnetic field in the vicinity of the CT453 sensor. The current sensor uses two full-bridge XtremeSense TMR sensors to achieve differential



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magnetic sensing capability, which allows the CT453 to greatly attenuate external magnetic fields and only capture the magnetic field generated by the current flowing in the busbar. Using this technique achieves better than -50 dB of CMFR without compromising the accuracy or the signal-to-noise ratio (SNR) of the CT453.

Figure 15 and Figure 16 shows an example of a 2-layer printed circuit board (PCB) where the CT453 is placed on the top layer of the PCB and the bottom layer is designed to generate differential magnetic fields as the current flows through this trace. The snake-like shape of the PCB trace produces the differential magnetic fields that almost completely eliminates the effects of stray magnetic fields to the CT453. This ensures that the CT453 outputs an accurate output voltage/current measurement to the host system.

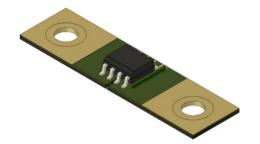
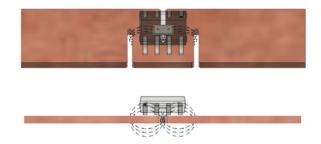


Figure 15: 3D View of CT453 and PCB Trace Design



### Figure 16: PCB Trace Design to Generate Differential Magnetic Field for CT453 to Measure

An exploded view of the differential magnetic field generated by the PCB trace is illustrated in Figure 17. It demonstrates the IP+ current generating a clockwise field and goes around the bend or corner of the trace and coming out is IP- with a counterclockwise field.



### Figure 17: Differential Magnetic Fields Generated Current Through the Busbar (or PCB Trace) and Measured by the CT453

This concept is not restricted to PCB layers and can be extended to busbars carrying current in the hundreds to thousands of amperes. Figure 18 shows a graphic of the CT453 placed over a busbar that generates differential magnetic fields when 300 A or greater steady-state current through it which will also give CMFR ratio of -50 dB or greater than 90% immunity.

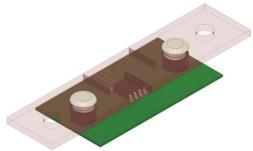


Figure 18: CT453 for Contactless Current Sensing Using Busbar

For more information on how to design the PCB trace and busbar to achieve this CMFR performance, see application note AN134, Fuse Time vs. Current for the CT43x Contact Current Sensors.

### **Sensitivity Error**

The sensitivity error  $(E_{SENS})$  is the sensitivity temperature drift error for unipolar or DC current. It is calculated using the equation below:

$$E_{SENS} = 100 \times \left(\frac{S_{MEASURED}}{S} - 1\right)$$

For bipolar or AC current, the  $\mathrm{E}_{\mathrm{SENS}}$  is calculated by dividing the equation by 2.

## Power-On Time (t<sub>ON</sub>)

Power-On Time ( $t_{ON}$ ) of 100  $\mu$ s is the amount of time required by CT453 to start up, fully power the chip, and becoming fully



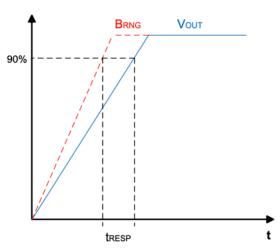
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operational from the moment the supply voltage is greater than the UVLO voltage. This time includes the ramp-up time and the settling time (within 10% of steady-state voltage under an applied magnetic field) after the power supply has reached the minimum  $V_{\rm CC}$ .

## Response Time (t<sub>RESPONSE</sub>)

Response Time ( $t_{RESPONSE}$ ) of 300 ns for the CT453 is the time interval between the following terms:

- 1. When the primary current signal reaches 90% of its final value.
- 2. When the chip reaches 90% of its output corresponding to the applied current.





### Rise Time (t<sub>RISE</sub>)

Rise Time ( $t_{RISE}$ ) is the time interval of when it reaches 10% and 90% of the full-scale output voltage. The  $t_{RISE}$  of the CT453 is 200 ns.

## Propagation Delay (t<sub>DELAY</sub>)

Propagation Delay  $(t_{DELAY})$  is the time difference between these two events:

- 1. When the primary current reaches 20% of its final value
- 2. When the chip reaches 20% of its output corresponding to the applied current.

The CT453 has a propagation delay of 250 ns.

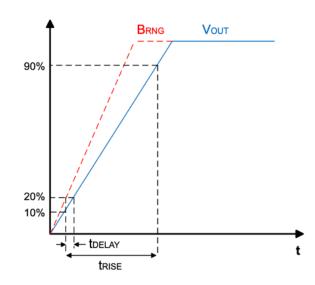


Figure 20: CT453 Propagation Delay and Rise Time Curve

## Undervoltage Lockout (UVLO)

The Undervoltage Lockout protection circuitry of the CT453 is activated when the supply voltage ( $V_{CC}$ ) falls below 2.45 V. The CT453 remains in a low quiescent state until  $V_{CC}$  rises above the UVLO threshold (2.50 V). In this condition where  $V_{CC}$  is less than 2.45 V and UVLO is triggered, the output from the CT453 is not valid. Once  $V_{CC}$  rises above 4.0 V, then the UVLO is cleared.

## **Recommended PCB Trace Design**

The CT453 requires a different PCB trace or busbar design than the standard current trace or busbar to enable common mode field rejection. Figure 21 and Figure 22 show the shape and design of a PCB trace or busbar.

Other considerations in the PCB layout include the thickness of the trace and the amount of copper to support the current. Also placing the PCB trace on the bottom layer of the board will increase the isolation voltage. The greater distance between the CT453 and the current trace will result in a higher isolation voltage.

For more information on how to design the current-carrying busbar or PCB trace, see AN135 application note, CT453/3 Busbar Design.



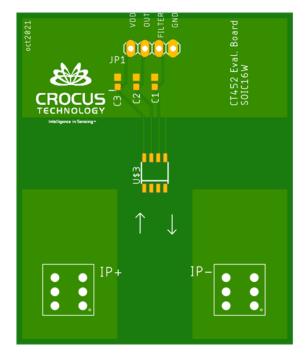


Figure 21: Recommended PCB Layout (Top Layer) for CT453

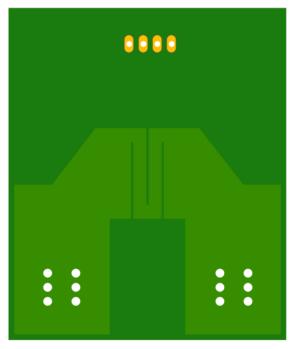


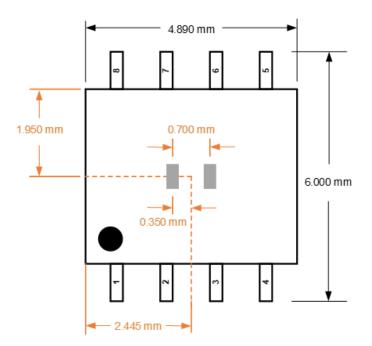
Figure 22: Recommended PCB Layout (Bottom Layer) for CT453

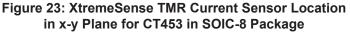


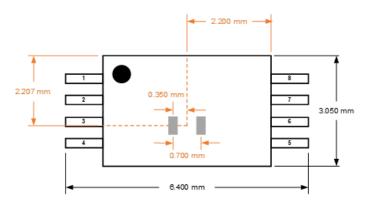
# XtremeSense™ TMR Coreless, Differential, and Contactless Current Sensor with Programmable Gain

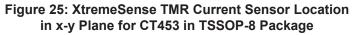
### **XtremeSense TMR Current Sensor Location**

The XtremeSense TMR current sensor location of the CT453 is shown below. All dimensions in the figures are nominal.









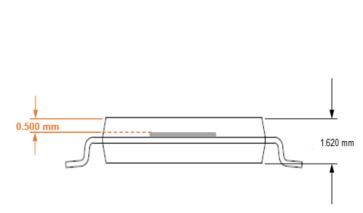


Figure 24: XtremeSense TMR Current Sensor Location in z Dimension for CT453 in SOIC-8 Package

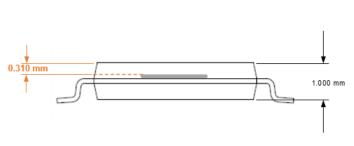


Figure 26: XtremeSense TMR Current Sensor Location in z Dimension for CT453 in TSSOP-8 Package

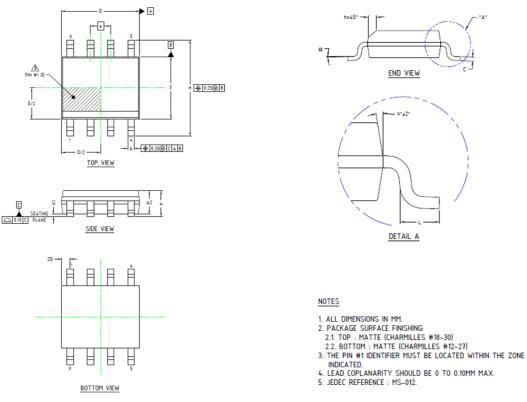


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### PACKAGE OUTLINE DRAWINGS

### For Reference Only – Not for Tooling Use

Dimensions in millimeters – NOT TO SCALE Dimensions exclusive of mold flash, gate burs, and dambar protrusions Exact case and lead configuration at supplier discretion within limits shown







Symbol		Dimensions in Millimeters (mm)		
Symbol	Min.	Тур.	Max.	
A1	0.10	0.18	0.25	
b	0.36	0.41	0.46	
С	0.19	0.22	0.25	
D	4.80	4.89	4.98	
E	3.81	3.90	3.99	
e	1.27 BSC			
Н	5.80	6.00	6.20	
h	0.25	0.37	0.50	
L	0.41	-	1.27	
A	1.52	1.62	1.72	
α	0°	_	8°	
ZD	0.53 REF			
A2	1.37	1.47	1.57	



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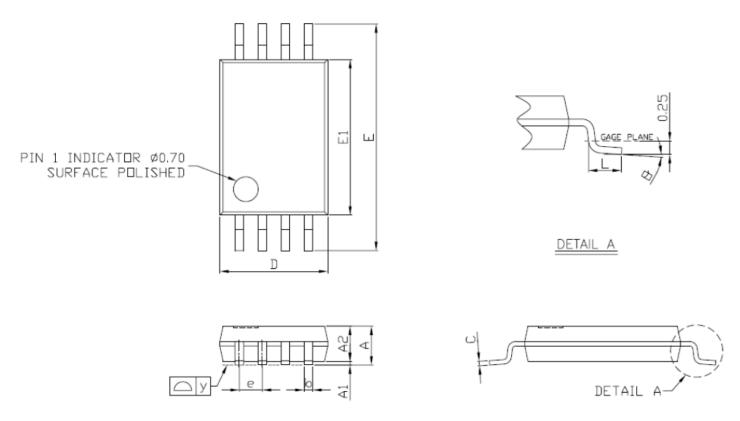


Figure 28: TSSOP-8 Package Drawing and Dimensions

### Table 4: CT453 TSSOP-8 Package Dimensions

Symbol		Dimensions in Millimeters (mm)	
Symbol	Min.	Тур.	Max.
A	1.05	1.10	1.20
A1	0.05	0.10	0.15
A2	_	1.00	1.05
b	0.25	_	0.30
С	_	0.127	-
D	2.90	3.05	3.10
E	6.20	6.40	6.60
E1	4.30	4.40	4.50
e	_	0.65	-
L	0.50	0.60	0.70
У	_	_	0.076
θ	0°	4°	8°



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### TAPE AND REEL POCKET DRAWINGS AND DIMENSIONS

For Reference Only – Not for Tooling Use Dimensions in millimeters – NOT TO SCALE Dimensions exclusive of mold flash, gate burs, and dambar protrusions Exact case and lead configuration at supplier discretion within limits shown

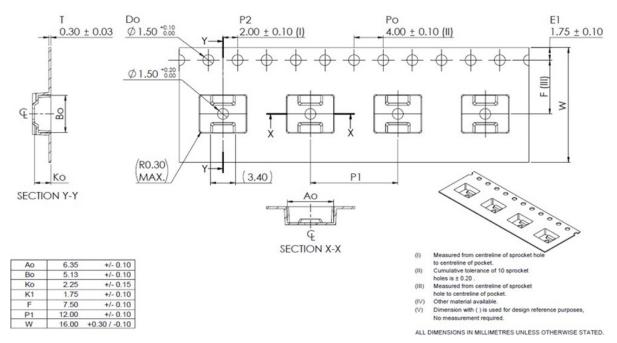


Figure 29: Tape and Pocket Drawing for SOIC-8 Package



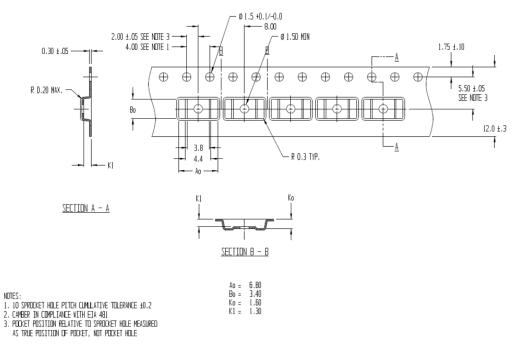


Figure 30: Tape and Pocket Drawing for TSSOP-8 Package



### PACKAGE INFORMATION

#### Table 5: CT453 Package Information

Part Number	Package Type	# of Leads	Package Quantity	Lead Finish	MSL Rating <sup>[2]</sup>	Operating Temperature (°C) <sup>[3]</sup>	Device Marking <sup>[4]</sup>
CT453-H06MRTS08	TSSOP	8	3000	Sn	1	-40 to 125	CT453-06MR YYWWLL
CT453-H06MRSN08	SOIC	8	2000	Sn	3	-40 to 125	CT453 06MR YYWWLL
CT453-H06DRTS08	TSSOP	8	3000	Sn	1	-40 to 125	CT453-06DR YYWWLL
CT453-H06DRSN08	SOIC	8	2000	Sn	3	-40 to 125	CT453 06DR YYWWLL
CT453-H00MRTS08	TSSOP	8	3000	Sn	1	-40 to 125	CT453-00MR YYWWLL
CT453-H00DRTS08	TSSOP	8	3000	Sn	1	-40 to 125	CT453-00DR YYWWLL
CT453-H00MRSN08	SOIC	8	2000	Sn	3	-40 to 125	CT453 00MR YYWWLL
CT453-H00DRSN08	SOIC	8	2000	Sn	3	-40 to 125	CT453 00DR YYWWLL

[1] RoHS is defined as semiconductor products that are compliant to the current EU RoHS requirements. It also will meet the requirement that RoHS substances do not exceed 0.1% by weight in homogeneous materials. Green is defined as the content of chlorine (CI), bromine (Br), and antimony trioxide based flame retardants satisfy JS709B low halogen requirements of ≤ 1,000 ppm.

<sup>[2]</sup> MSL Rating = Moisture Sensitivity Level Rating as defined by JEDEC standard classifications.

<sup>[3]</sup> Package will withstand ambient temperature range of -40°C to 125°C and storage temperature range of -65°C to 150°C.

[4] For the CT453, device marking for the SOIC-8 is defined as CT453 xxZR YYWWLL where the first 2 lines = part number, and third line is YY = year, WW = work week, and LL = lot code. Device marking for the TSSOP-8 is defined as CT450 xxZR YYWWLL where the first line = part number, and second line is YY = year, WW = work week, and LL = lot code.



## **DEVICE MARKINGS**

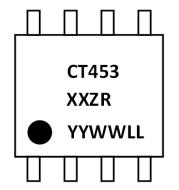


Figure 31: CT453 Device Marking for 8-Lead SOIC Package

Row No.	Code	Definition		
3	•	Pin 1 Indicator		
1	CT453	Allegro Part Number		
2	XX	Maximum Field Rating		
2	ZR Polarity			
3	YY	Calendar Year		
3	WW Work Week			
3	LL	Lot Code		

#### Table 6: CT453 Device Marking Definition for 8-lead SOIC Package

1		8
2	CT453-XXZR	7
3	YYWWLL	6
4		5

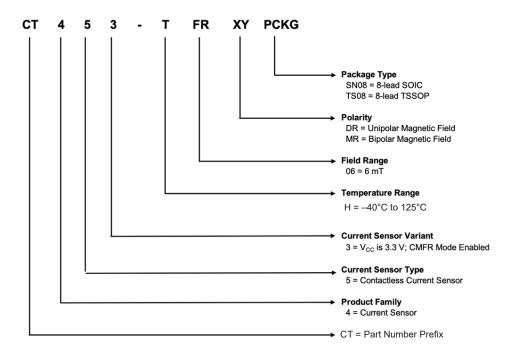
Figure 32: CT453 Device Marking for 8-Lead TSSOP Package

#### Table 7: CT453 Device Marking Definition for 8-lead TSSOP Package

Row No.	Code	Definition
1	•	Pin 1 Indicator
2	CT453 Allegro Part Number	
2	XX Maximum Magnetic Field Rating	
2	ZR	Magnetic Field Range
3	YY	Calendar Year
3	WW	Work Week
3	LL	Lot Code



### PART ORDERING NUMBER LEGEND





#### **Revision History**

Number	Date	Description
1	November 2, 2023	Document rebranded and minor editorial updates
2	February 15, 2024	Removed AEC-Q100 (pages 1, 2, 21-23) and updated Selection Guide (page 2) and MSL levels (page 21)
3	February 29, 2024	Updated Offset Voltage (pages 9-12); removed Out Accuracy Performance and Lifetime Drift footnotes (pages 9-12); updated Sensitivity and removed Noise (pages 11-12); and updated branding information (page 22)
4	June 5, 2024	Added notes to package drawings (pages 18 and 20)
5	September 19, 2024	Updated Description section (page 1); updated Electrical Characteristics figures (pages 9, 10); updated Electrical Characteristics tables (pages 9-12); updated Functional Description overview section (page 13); removed Total Output Error section (pages 13, 14)

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